

Zainuriah Hassan

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535
papers

6,068
citations

37
h-index

54
g-index

598
ext. papers

6,846
ext. citations

2.7
avg, IF

6.29
L-index

#	Paper	IF	Citations
535	InGaN: An overview of the growth kinetics, physical properties and emission mechanisms. <i>Superlattices and Microstructures</i> , 2008 , 43, 1-23	2.8	178
534	Innovative advances in LED technology. <i>Microelectronics Journal</i> , 2005 , 36, 129-137	1.8	142
533	An image encryption scheme based on quantum logistic map. <i>Communications in Nonlinear Science and Numerical Simulation</i> , 2012 , 17, 4653-4661	3.7	126
532	A high-sensitivity room-temperature hydrogen gas sensor based on oblique and vertical ZnO nanorod arrays. <i>Sensors and Actuators B: Chemical</i> , 2013 , 176, 360-367	8.5	120
531	Pseudo random number generator based on quantum chaotic map. <i>Communications in Nonlinear Science and Numerical Simulation</i> , 2014 , 19, 101-111	3.7	111
530	A novel scheme for image encryption based on 2D piecewise chaotic maps. <i>Optics Communications</i> , 2010 , 283, 3259-3266	2	108
529	High sensitivity and fast response and recovery times in a ZnO nanorod array/p-Si self-powered ultraviolet detector. <i>Applied Physics Letters</i> , 2012 , 101, 261108	3.4	84
528	Structural and optical properties of nanocrystalline CdS thin films prepared using microwave-assisted chemical bath deposition. <i>Thin Solid Films</i> , 2012 , 520, 3477-3484	2.2	83
527	High-quality vertically aligned ZnO nanorods synthesized by microwave-assisted CBD with ZnOBVA complex seed layer on Si substrates. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 6711-6719	5.7	77
526	Room temperature hydrogen gas sensor based on ZnO nanorod arrays grown on a SiO ₂ /Si substrate via a microwave-assisted chemical solution method. <i>Journal of Alloys and Compounds</i> , 2013 , 546, 107-111	5.7	73
525	A high-sensitivity, fast-response, rapid-recovery UV photodetector fabricated based on catalyst-free growth of ZnO nanowire networks on glass substrate. <i>Optical Materials</i> , 2016 , 60, 30-37	3.3	67
524	Fabrication and characterization of V ₂ O ₅ nanorods based metal-semiconductor-metal photodetector. <i>Sensors and Actuators A: Physical</i> , 2016 , 250, 250-257	3.9	63
523	Synthesis and characterization of single-crystal CdS nanosheet for high-speed photodetection. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 44, 1716-1721	3	62
522	New optical features to enhance solar cell performance based on porous silicon surfaces. <i>Applied Surface Science</i> , 2011 , 257, 6112-6117	6.7	62
521	Effective conversion efficiency enhancement of solar cell using ZnO/PS antireflection coating layers. <i>Solar Energy</i> , 2012 , 86, 541-547	6.8	61
520	Enhancement of optical transmittance and electrical resistivity of post-annealed ITO thin films RF sputtered on Si. <i>Applied Surface Science</i> , 2018 , 443, 544-547	6.7	59
519	Highly sensitive fast-response UV photodiode fabricated from rutile TiO ₂ nanorod array on silicon substrate. <i>Sensors and Actuators A: Physical</i> , 2015 , 221, 15-21	3.9	57

518	A high-sensitivity, fast-response, rapid-recovery p-n heterojunction photodiode based on rutile TiO ₂ nanorod array on p-Si(1 1 1). <i>Applied Surface Science</i> , 2014 , 305, 445-452	6.7	56
517	Effects of Postdeposition Annealing in Argon Ambient on Metallorganic Decomposed CeO ₂ Gate Spin Coated on Silicon. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H6	3.9	52
516	Fabrication and characterisations of n-CdS/p-PbS heterojunction solar cells using microwave-assisted chemical bath deposition. <i>Solar Energy</i> , 2013 , 89, 143-151	6.8	50
515	High performance room temperature GaN-nanowires hydrogen gas sensor fabricated by chemical vapor deposition (CVD) technique. <i>International Journal of Hydrogen Energy</i> , 2013 , 38, 14085-14101	6.7	49
514	The effect of etching time of porous silicon on solar cell performance. <i>Superlattices and Microstructures</i> , 2011 , 50, 647-658	2.8	48
513	Morphological, optical, and Raman characteristics of ZnO nanoflakes prepared via a sol-gel method. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012 , 209, 143-147	1.6	46
512	Schottky diode based on porous GaN for hydrogen gas sensing application. <i>Applied Surface Science</i> , 2007 , 253, 9525-9528	6.7	46
511	High Al-content Al _x Ga _{1-x} N epilayers grown on Si substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2009 , 487, 24-27	5.7	45
510	Fabrication and characterization of metal-semiconductor-metal ultraviolet photodetector based on rutile TiO ₂ nanorod. <i>Materials Research Bulletin</i> , 2016 , 73, 29-37	5.1	44
509	Fabrication of low cost UV photo detector using ZnO nanorods grown onto nylon substrate. <i>Journal of Materials Science: Materials in Electronics</i> , 2015 , 26, 1322-1331	2.1	43
508	Sm ₂ O ₃ gate dielectric on Si substrate. <i>Materials Science in Semiconductor Processing</i> , 2010 , 13, 303-314	4.3	41
507	Effects of oxygen percentage on the growth of copper oxide thin films by reactive radio frequency sputtering. <i>Materials Chemistry and Physics</i> , 2013 , 140, 243-248	4.4	40
506	Porous GaN on Si(111) and its application to hydrogen gas sensor. <i>Sensors and Actuators B: Chemical</i> , 2011 , 155, 699-708	8.5	40
505	High performance CuS p-type thin film as a hydrogen gas sensor. <i>Sensors and Actuators A: Physical</i> , 2016 , 249, 68-76	3.9	40
504	Structural and photoluminescence studies of rutile TiO ₂ nanorods prepared by chemical bath deposition method on Si substrates at different pH values. <i>Measurement: Journal of the International Measurement Confederation</i> , 2014 , 56, 155-162	4.6	39
503	Hydrogen gas sensing performance of GaN nanowires-based sensor at low operating temperature. <i>Sensors and Actuators B: Chemical</i> , 2014 , 204, 497-506	8.5	39
502	Fabrication and characterization of ZnO nanorods/p-6H ₆ BiC heterojunction LED by microwave-assisted chemical bath deposition. <i>Superlattices and Microstructures</i> , 2013 , 53, 31-38	2.8	39
501	Growth of CdS nanosheets and nanowires through the solvothermal method. <i>Journal of Crystal Growth</i> , 2012 , 359, 43-48	1.6	38

500	Characterization of nanocrystalline PbS thin films prepared using microwave-assisted chemical bath deposition. <i>Materials Science in Semiconductor Processing</i> , 2012 , 15, 564-571	4.3	38
499	Porous GaN prepared by UV assisted electrochemical etching. <i>Thin Solid Films</i> , 2007 , 515, 3469-3474	2.2	38
498	Fabrication and characterization of nanocrystalline CdS thin film-based optical sensor grown via microwave-assisted chemical bath deposition. <i>Superlattices and Microstructures</i> , 2014 , 67, 8-16	2.8	37
497	Growth of zinc oxide nanoflowers by thermal evaporation method. <i>Physica B: Condensed Matter</i> , 2010 , 405, 2570-2572	2.8	36
496	The study of Pt Schottky contact on porous GaN for hydrogen sensing. <i>Thin Solid Films</i> , 2007 , 515, 7337-7341	2.4	36
495	Microwave-assisted chemical bath deposition of nanocrystalline CdS thin films with superior photodetection characteristics. <i>Sensors and Actuators A: Physical</i> , 2015 , 230, 9-16	3.9	35
494	Growth and characterization of CdS single-crystalline micro-rod photodetector. <i>Superlattices and Microstructures</i> , 2013 , 54, 137-145	2.8	35
493	ZnO nanocoral reef grown on porous silicon substrates without catalyst. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 5627-5630	5.7	35
492	Growth and characterization of Zn _x Cd _{1-x} S nanoflowers by microwave-assisted chemical bath deposition. <i>Journal of Alloys and Compounds</i> , 2012 , 541, 227-233	5.7	34
491	Structural and optical characteristics of porous GaN generated by electroless chemical etching. <i>Materials Letters</i> , 2009 , 63, 724-727	3.3	34
490	The effect of anti-reflection coating of porous silicon on solar cells efficiency. <i>Optik</i> , 2011 , 122, 1462-1465	5.5	33
489	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO ₂) gate deposited on GaN and SiC substrates. <i>Journal of Crystal Growth</i> , 2011 , 326, 2-8	1.6	33
488	Characterization of surface roughness of Pt Schottky contacts on quaternary n-Al _{0.08} In _{0.08} Ga _{0.84} N thin film assessed by atomic force microscopy and fractal analysis. <i>Journal of Materials Science: Materials in Electronics</i> , 2014 , 25, 466-477	2.1	32
487	Experimental and theoretical studies of surface phonon polariton of AlN thin film. <i>Applied Physics Letters</i> , 2007 , 90, 081902	3.4	32
486	Study of efficient semipolar (11-22) InGa _N green micro-light-emitting diodes on high-quality (11-22) GaN/sapphire template. <i>Optics Express</i> , 2019 , 27, 24154-24160	3.3	31
485	Preparation of chemically deposited thin films of CdS/PbS solar cell. <i>Superlattices and Microstructures</i> , 2012 , 52, 816-823	2.8	30
484	Comparative study of ultraviolet detectors based on ZnO nanostructures grown on different substrates. <i>Journal of Applied Physics</i> , 2012 , 112, 074510	2.5	30
483	Effects of ZnO seed layer thickness on catalyst-free growth of ZnO nanostructures for enhanced UV photoresponse. <i>Optics and Laser Technology</i> , 2018 , 98, 344-353	4.2	29

482	PbS nanocrystal solar cells fabricated using microwave-assisted chemical bath deposition. <i>International Journal of Hydrogen Energy</i> , 2013 , 38, 807-815	6.7	29
481	Quaternary ultraviolet AlInGaN MQW laser diode performance using quaternary AlInGaN electron blocking layer. <i>Optics Express</i> , 2011 , 19, 9245-54	3.3	29
480	Porous Si(1 1 1) and Si(1 0 0) as an intermediate buffer layer for nanocrystalline InN films. <i>Journal of Alloys and Compounds</i> , 2009 , 479, L54-L58	5.7	29
479	Structural, optical and electrical characterization of ITO, ITO/Ag and ITO/Ni transparent conductive electrodes. <i>Applied Surface Science</i> , 2014 , 288, 599-603	6.7	28
478	Influence of deposition temperature on the growth of rutile TiO ₂ nanostructures by CBD method on seed layer prepared by RF magnetron sputtering. <i>Superlattices and Microstructures</i> , 2013 , 64, 27-36	2.8	28
477	The structural and optical characterizations of ZnO synthesized using the Bottom-up growth method. <i>Physica B: Condensed Matter</i> , 2010 , 405, 2045-2048	2.8	28
476	Effect of Postdeposition Annealing in Oxygen Ambient on Gallium-Nitride-Based MOS Capacitors With Cerium Oxide Gate. <i>IEEE Transactions on Electron Devices</i> , 2011 , 58, 122-131	2.9	27
475	Hash function based on hierarchy of 2D piecewise nonlinear chaotic maps. <i>Chaos, Solitons and Fractals</i> , 2009 , 42, 2405-2412	9.3	26
474	Ultrathin Wafer Pre-Assembly and Assembly Process Technologies: A Review. <i>Critical Reviews in Solid State and Materials Sciences</i> , 2015 , 40, 251-290	10.1	25
473	Fabrication of a highly flexible low-cost H ₂ gas sensor using ZnO nanorods grown on an ultra-thin nylon substrate. <i>Journal of Materials Science: Materials in Electronics</i> , 2016 , 27, 9461-9469	2.1	25
472	Investigation of forming-gas annealed CeO ₂ thin film on GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 583-591	2.1	24
471	Optical properties of CdS micro/nanocrystalline structures prepared via a thermal evaporation method. <i>Materials Science in Semiconductor Processing</i> , 2014 , 26, 87-92	4.3	23
470	Fabrication of ZnO nanorod/p-GaN high-brightness UV LED by microwave-assisted chemical bath deposition with Zn(OH) ₂ /PVA nanocomposites as seed layer. <i>Optical Materials</i> , 2013 , 35, 1035-1041	3.3	23
469	Growth and conversion of Ga ₂ O ₃ nanobelts into GaN nanowires via catalyst-free chemical vapor deposition technique. <i>Superlattices and Microstructures</i> , 2013 , 54, 215-224	2.8	23
468	Microwave assisted chemical bath deposition of vertically aligned ZnO nanorods on a variety of substrates seeded by PVA/n(OH) ₂ nanocomposites. <i>Applied Surface Science</i> , 2012 , 258, 4467-4472	6.7	23
467	Surface and interface phonon polaritons of wurtzite GaN thin film grown on 6H-SiC substrate. <i>Applied Physics Letters</i> , 2009 , 94, 241912	3.4	23
466	Influences of substrate type on the pH sensitivity of CuS thin films EGFET prepared by spray pyrolysis deposition. <i>Materials Science in Semiconductor Processing</i> , 2017 , 63, 269-278	4.3	22
465	MBE growth of GaN pn-junction photodetector on AlN/Si(1 1 1) substrate with Ni/Ag as ohmic contact. <i>Superlattices and Microstructures</i> , 2013 , 56, 35-44	2.8	22

464	Alteration of structural and optical properties in quaternary Al _{0.1} In _{0.1} Ga _{0.8} N films using ultraviolet assisted photo-electrochemical etching route. <i>Journal of Alloys and Compounds</i> , 2015 , 649, 337-347	5.7	21
463	Growth and characterization of rutile TiO ₂ nanorods on various substrates with fabricated fast-response metal-semiconductor-metal UV detector based on Si substrate. <i>Superlattices and Microstructures</i> , 2015 , 83, 549-564	2.8	21
462	Free growth of one-dimensional Ga ₂ O ₃ nanostructures including nanowires, nanobelts and nanosheets using a thermal evaporation method. <i>Ceramics International</i> , 2016 , 42, 13343-13349	5.1	21
461	Catalyst-free growth of ZnO nanowires on ITO seed layer/glass by thermal evaporation method: Effects of ITO seed layer laser annealing temperature. <i>Superlattices and Microstructures</i> , 2016 , 92, 68-79	2.8	21
460	Improved performance of solar cell based on porous silicon surfaces. <i>Optik</i> , 2011 , 122, 2075-2077	2.5	21
459	Effects of N ₂ O Postdeposition Annealing on Metal-Organic Decomposed CeO ₂ Gate Oxide Spin-Coated on GaN Substrate. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H423	3.9	21
458	Characterizations of InN Thin Films Grown on Si (110) Substrate by Reactive Sputtering. <i>Journal of Nanomaterials</i> , 2011 , 2011, 1-7	3.2	21
457	Surface phonon polariton of wurtzite GaN thin film grown on -plane sapphire substrate. <i>Solid State Communications</i> , 2008 , 145, 535-538	1.6	21
456	High-performance p-n heterojunction photodetectors based on V ₂ O ₅ nanorods by spray pyrolysis. <i>Applied Physics A: Materials Science and Processing</i> , 2016 , 122, 1	2.6	21
455	Effects of thermal treatment on the anodic growth of tungsten oxide films. <i>Thin Solid Films</i> , 2015 , 588, 44-49	2.2	20
454	Effects of ammonia-ambient annealing on physical and electrical characteristics of rare earth CeO ₂ as passivation film on silicon. <i>Journal of Alloys and Compounds</i> , 2017 , 695, 3104-3115	5.7	20
453	Fabrication and characterization of nanocrystalline n-CdO/p-Si as a solar cell. <i>Superlattices and Microstructures</i> , 2012 , 52, 800-806	2.8	20
452	Structural and optical properties of nanocrystalline lead sulfide thin films prepared by microwave-assisted chemical bath deposition. <i>Materials Science in Semiconductor Processing</i> , 2013 , 16, 971-979	4.3	20
451	Porous silicon nanowires fabricated by electrochemical and laser-induced etching. <i>Journal of Materials Science: Materials in Electronics</i> , 2011 , 22, 717-723	2.1	20
450	Structural Properties of Doped GaN on Si(111) Studied by X-Ray Diffraction Techniques. <i>Journal of Nondestructive Evaluation</i> , 2009 , 28, 125-130	2.1	20
449	Investigation of structural and optical properties of nanoporous GaN film. <i>Applied Surface Science</i> , 2007 , 253, 7429-7434	6.7	20
448	Effect of hydrostatic pressure on the barrier height of Ni Schottky contacts on n-AlGaIn. <i>Applied Physics Letters</i> , 2006 , 88, 022109	3.4	20
447	Pt-decorated GaN nanowires with significant improvement in H ₂ gas-sensing performance at room temperature. <i>Journal of Colloid and Interface Science</i> , 2015 , 460, 135-45	9.3	19

446	Nanocrystalline ZnO film grown on porous silicon layer by radio frequency sputtering system. <i>Materials Letters</i> , 2012 , 68, 51-53	3.3	19
445	Influence of CuS membrane annealing time on the sensitivity of EGFET pH sensor. <i>Materials Science in Semiconductor Processing</i> , 2017 , 71, 217-225	4.3	19
444	Characterization Methods for Ultrathin Wafer and Die Quality: A Review. <i>IEEE Transactions on Components, Packaging and Manufacturing Technology</i> , 2014 , 4, 2042-2057	1.7	19
443	MOS Characteristics of Metallorganic-Decomposed CeO ₂ Spin-Coated on GaN. <i>Electrochemical and Solid-State Letters</i> , 2010 , 13, H116		19
442	Surface phonon polariton mode of wurtzite structure Al _x Ga _{1-x} N (0 ≤ x ≤ 1) thin films. <i>Applied Physics Letters</i> , 2007 , 91, 081909	3.4	19
441	Growth of GaN on sputtered GaN buffer layer via low cost and simplified sol-gel spin coating method. <i>Vacuum</i> , 2015 , 119, 119-122	3.7	18
440	Synthesis of wurtzite GaN thin film via spin coating method. <i>Materials Science in Semiconductor Processing</i> , 2014 , 17, 63-66	4.3	18
439	Effects of annealing on the optical and electrical properties of CdO thin films prepared by thermal evaporation. <i>Materials Letters</i> , 2013 , 105, 84-86	3.3	18
438	Enhancing photoresponse time of low cost Pd/ZnO nanorods prepared by thermal evaporation techniques for UV detection. <i>Applied Surface Science</i> , 2011 , 258, 461-465	6.7	18
437	Effect of Al mole fraction on structural and electrical properties of Al _x Ga _{1-x} N/GaN heterostructures grown by plasma-assisted molecular beam epitaxy. <i>Applied Surface Science</i> , 2011 , 257, 4159-4164	6.7	18
436	Effect of zinc acetate dihydrate concentration on morphology of ZnO seed layer and ZnO nanorods grown by hydrothermal method. <i>Colloids and Interface Science Communications</i> , 2020 , 38, 100312	5.4	18
435	Rapid Formation and Evolution of Anodized-Zn Nanostructures in NaHCO ₃ Solution. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, M105-M112	2	18
434	Large-scale uniform ZnO tetrapods on catalyst free glass substrate by thermal evaporation method. <i>Materials Research Bulletin</i> , 2016 , 79, 63-68	5.1	17
433	Effect of different EBL structures on deep violet InGaN laser diodes performance. <i>Optics and Laser Technology</i> , 2016 , 76, 106-112	4.2	17
432	Improvement of the performance characteristics of deep violet InGaN multi-quantum-well laser diodes using step-graded electron blocking layers and a delta barrier. <i>Journal of Applied Physics</i> , 2013 , 113, 123108	2.5	17
431	Effect of Annealing Time of YAG:Ce ³⁺ Phosphor on White Light Chromaticity Values. <i>Journal of Electronic Materials</i> , 2018 , 47, 1638-1646	1.9	17
430	Effect of Annealing on the Electrical Properties of Cu _x S Thin Films. <i>Procedia Chemistry</i> , 2016 , 19, 15-20		16
429	Porous WO ₃ formed by anodization in oxalic acid. <i>Journal of Porous Materials</i> , 2013 , 20, 997-1002	2.4	16

428	Synthesis of two-dimensional gallium nitride via spin coating method: influences of nitridation temperatures. <i>Journal of Sol-Gel Science and Technology</i> , 2013 , 68, 95-101	2.3	16
427	Analytical and visual modeling of InGaN/GaN single quantum well laser based on rate equations. <i>Optics and Laser Technology</i> , 2012 , 44, 12-20	4.2	16
426	Surface phonon polariton characteristic of honeycomb nanoporous GaN thin films. <i>Applied Physics Letters</i> , 2013 , 102, 101601	3.4	16
425	Stiffness properties of porous silicon nanowires fabricated by electrochemical and laser-induced etching. <i>Superlattices and Microstructures</i> , 2011 , 50, 119-127	2.8	16
424	Al _x Ga _{1-x} N/GaN/AlN heterostructures grown on Si(111) substrates by MBE for MSM UV photodetector applications. <i>Materials Science in Semiconductor Processing</i> , 2015 , 34, 214-223	4.3	15
423	Sensitivity of CuS and CuS/ITO EGFETs implemented as pH sensors. <i>Applied Physics A: Materials Science and Processing</i> , 2016 , 122, 1	2.6	15
422	Growth and characterization of different structured CdO using a vapor transport. <i>Materials Letters</i> , 2013 , 102-103, 12-14	3.3	15
421	Effect of temperature on hydrothermally grown high-quality single-crystals Mg-doped ZnO nanorods for light-emitting diode application. <i>Journal of Luminescence</i> , 2017 , 192, 634-643	3.8	15
420	Fast UV detection and hydrogen sensing by ZnO nanorod arrays grown on a flexible Kapton tape. <i>Materials Science-Poland</i> , 2013 , 31, 180-185	0.6	15
419	Sensing devices based on ZnO hexagonal tube-like nanostructures grown on p-GaN heterojunction by wet thermal evaporation. <i>Thin Solid Films</i> , 2013 , 540, 212-220	2.2	15
418	Fabrication of InN based photodetector using porous silicon buffer layer. <i>Surface Engineering</i> , 2013 , 29, 772-777	2.6	15
417	Improved performance of a crystalline silicon solar cell based on ZnO/PS anti-reflection coating layers. <i>Superlattices and Microstructures</i> , 2011 , 50, 517-528	2.8	15
416	GaN Schottky barrier photodiode on Si (111) with low-temperature-grown cap layer. <i>Journal of Alloys and Compounds</i> , 2009 , 481, L15-L19	5.7	15
415	Synthesis and characterization of nanocrystalline CdS thin films for highly photosensitive self-powered photodetector. <i>EPJ Applied Physics</i> , 2016 , 74, 10101	1.1	14
414	Structural and optical properties of In-doped ZnO thin films under wet annealing. <i>Materials Letters</i> , 2014 , 116, 396-398	3.3	14
413	High sensitivity extended gate effect transistor based on V ₂ O ₅ nanorods. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 1364-1369	2.1	14
412	Characteristics of MSM photodetector fabricated on porous In _{0.08} Ga _{0.92} N. <i>Measurement: Journal of the International Measurement Confederation</i> , 2014 , 50, 172-174	4.6	14
411	The growth of III-V nitrides heterostructure on Si substrate by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2010 , 506, 343-346	5.7	14

410	Performance and optical characteristic of InGaN MQWs laser diodes. <i>Optics Express</i> , 2007 , 15, 2380-90	3.3	14
409	Fabrication of Tungsten Oxide Nanostructure by Sol-Gel Method. <i>Procedia Chemistry</i> , 2016 , 19, 113-118		14
408	Low-power UV photodetection characteristics of ZnO tetrapods grown on catalyst-free glass substrate. <i>Sensors and Actuators A: Physical</i> , 2016 , 250, 187-194	3.9	14
407	Novel SnO ₂ -coated ZnO nanostructures for room temperature hydrogen gas sensor. <i>International Journal of Hydrogen Energy</i> , 2021 , 46, 7000-7010	6.7	14
406	Laser-induced solution combustion of nano-Y ₂ O ₃ :0.04Ce phosphors and their fluorescent properties for white light conversion. <i>Journal of Alloys and Compounds</i> , 2017 , 711, 42-50	5.7	13
405	Cost-effective single-step carbon nanotube synthesis using microwave oven. <i>Materials Research Express</i> , 2017 , 4, 085602	1.7	13
404	High carrier concentrations of n- and p-doped GaN on Si(111) by nitrogen plasma-assisted molecular-beam epitaxy. <i>Journal of Materials Research</i> , 2007 , 22, 2623-2630	2.5	13
403	A comparative study of the electrical characteristics of metal-semiconductor-metal (MSM) photodiodes based on GaN grown on silicon. <i>Applied Surface Science</i> , 2005 , 249, 91-96	6.7	13
402	Effect of Light on the Sensitivity of CuS Thin Film EGFET Implemented as pH Sensor. <i>International Journal of Electrochemical Science</i> , 2016 , 4380-4388	2.2	13
401	Fabrication of titanium dioxide nanotubes in fluoride-free electrolyte via rapid breakdown anodization. <i>Journal of Porous Materials</i> , 2015 , 22, 1437-1444	2.4	12
400	AlN/GaN/AlN heterostructures grown on Si substrate by plasma-assisted MBE for MSM UV photodetector applications. <i>Materials Science in Semiconductor Processing</i> , 2015 , 29, 231-237	4.3	12
399	Characterization of V ₂ O ₅ nanorods grown by spray pyrolysis technique. <i>Journal of Materials Science: Materials in Electronics</i> , 2016 , 27, 4613-4621	2.1	12
398	Growth and characterization of silicon nanowires catalyzed by Zn metal via Pulsed Plasma-Enhanced Chemical Vapor Deposition. <i>Superlattices and Microstructures</i> , 2014 , 68, 90-100	2.8	12
397	Room-temperature synthesis of nanocrystalline titanium dioxide via electrochemical anodization. <i>Materials Science in Semiconductor Processing</i> , 2014 , 26, 130-136	4.3	12
396	Low fraction of hexagonal inclusions in thick and bulk cubic GaN layers. <i>Applied Surface Science</i> , 2014 , 317, 1010-1014	6.7	12
395	Effect of annealing temperature on IR-detectors based on InN nanostructures. <i>Vacuum</i> , 2014 , 106, 46-48	3.7	12
394	Nano and micro porous GaN characterization using image processing method. <i>Optik</i> , 2012 , 123, 1074-1078	3.8	12
393	Simulation and optimization of deep violet InGaN double quantum well laser. <i>Optics Communications</i> , 2012 , 285, 746-750	2	12

392	Structural and optical properties of Au-catalyzed SiNWs grown using pulsed plasma-enhanced chemical vapour deposition. <i>Superlattices and Microstructures</i> , 2013 , 61, 134-145	2.8	12
391	Fabrication of Cu ₂ O nanocrystalline thin films photosensor prepared by RF sputtering technique. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2017 , 94, 132-138	3	12
390	Room-temperature hydrogen gas sensor with ZnO nanorod arrays grown on a quartz substrate. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012 , 46, 254-258	3	12
389	The growth of heavily Mg-doped GaN thin film on Si substrate by molecular beam epitaxy. <i>Thin Solid Films</i> , 2011 , 520, 756-760	2.2	12
388	Strong coupling of sapphire surface polariton with aluminum nitride film phonon. <i>Physics Letters, Section A: General, Atomic and Solid State Physics</i> , 2009 , 373, 2382-2384	2.3	12
387	Effect of post-deposition annealing temperature on CeO ₂ thin film deposited on silicon substrate via RF magnetron sputtering technique. <i>Materials Science in Semiconductor Processing</i> , 2011 , 14, 101-107	4.3	12
386	Studies of surface and interface phonon polariton characteristics of wurtzite ZnO thin film on wurtzite 6H-SiC substrate by p-polarized infrared attenuated total reflection spectroscopy. <i>Thin Solid Films</i> , 2011 , 519, 3703-3708	2.2	12
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